

C395V-110

UV LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaN on Si Substrate
Top Side Electrode/N(Cathode)	Au Alloy
Bottom Side Electrode/P(Anode)	AuSn Alloy
Chip Size	1140umx1140um typical
Chip Thickness	150um typical
Pad Diameter	130um typical

Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Forward Current	IF	750	mW
	IFP*	1000	mA
Reverse Voltage	VR	5	V
Operating Temperature	TOPR	-40 ~ +85	°C
Storage Temperature	TSTG	-40 ~ +60	°C

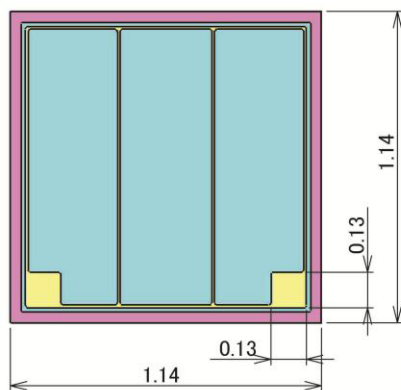
- Pulse Forward Current condition: Duty=1% x Pulse Width=10us

Electro-Optical Characteristics [Ta=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=500mA		3.3	4.5	V
Radiated Power	PO	IF=500mA		800		mW
Peak Wavelength	λP	IF=500mA	390	395	400	nm
FWHM	$\Delta\lambda$	IF=500mA		13		nm

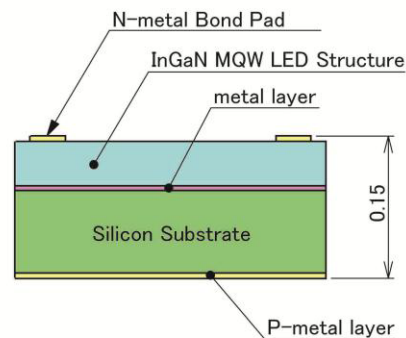
- Po minimum depends on wavelength

- Die shall be mounted on TO-18 gold header or SMB package without resin coated. (Ta=25°C)

<Chip Diagram:mm>

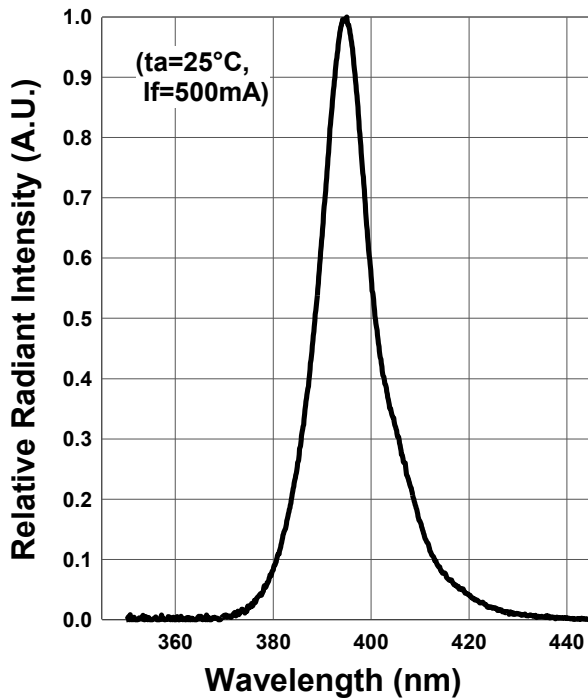


Chip pattern

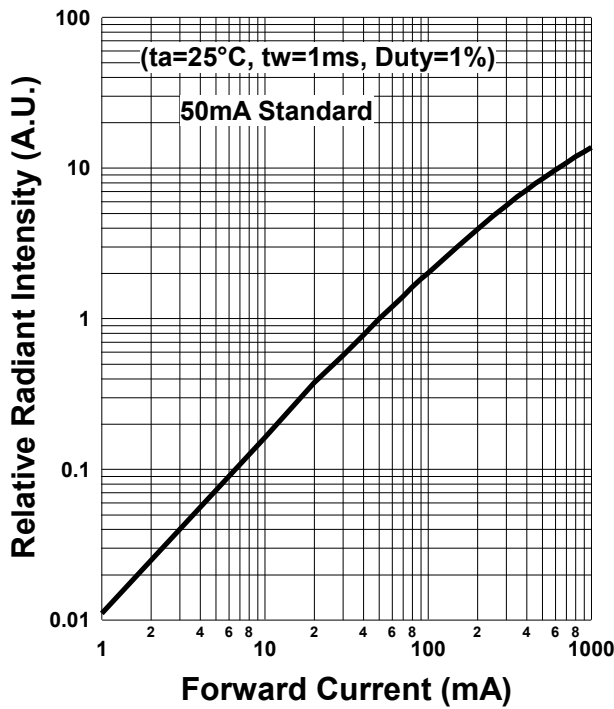


Chip Side View

Relative Spectral Emission



Relative Radiant Intensity - Forward Current



Forward Current - Forward Voltage

